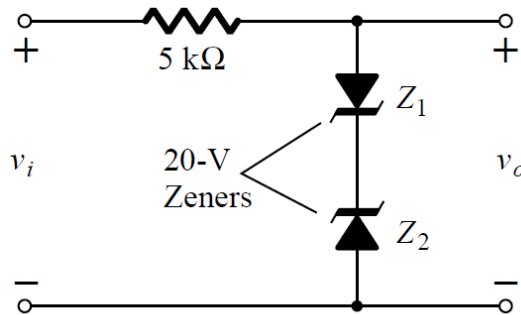

EHB222E INTRODUCTION TO ELECTRONICS (22985, 22982, 22986, 22984)

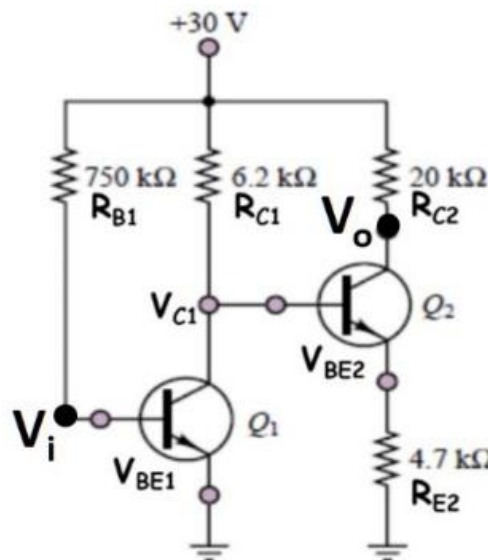
Midterm Exam #2  **16 May 2022**  **09:00-11:00**

Bora DÖKEN, Bülent YAĞCI, Hacer ATAR YILDIZ, İnci ÇİLESİZ

1. Calculate the peak voltage values for both half cycles of the output waveform. $V_1 = 20 \sin(2\pi \cdot 200 \cdot t)$. Use modified ideal diode model ($V_d = 0.7V$) for diodes. (5 points)

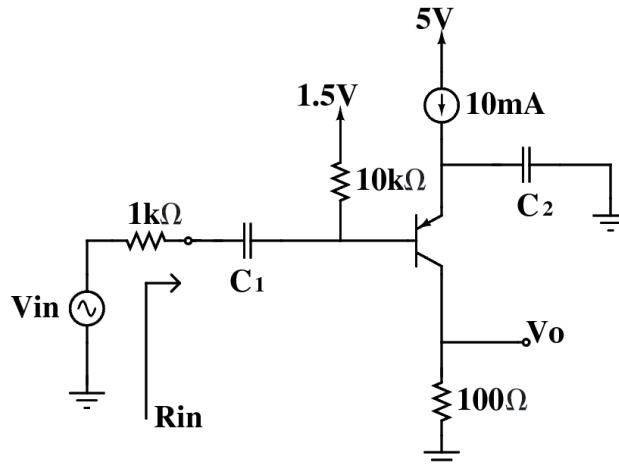


2. Consider the circuit shown below. Use the following transistor parameters for your calculations: $h_{FE} = \beta = 100$, $|V_{BE}| = 0.7V$, $V_T = 25mV$, $V_A = \infty$. Calculate the input impedance of the circuit. (10 points)

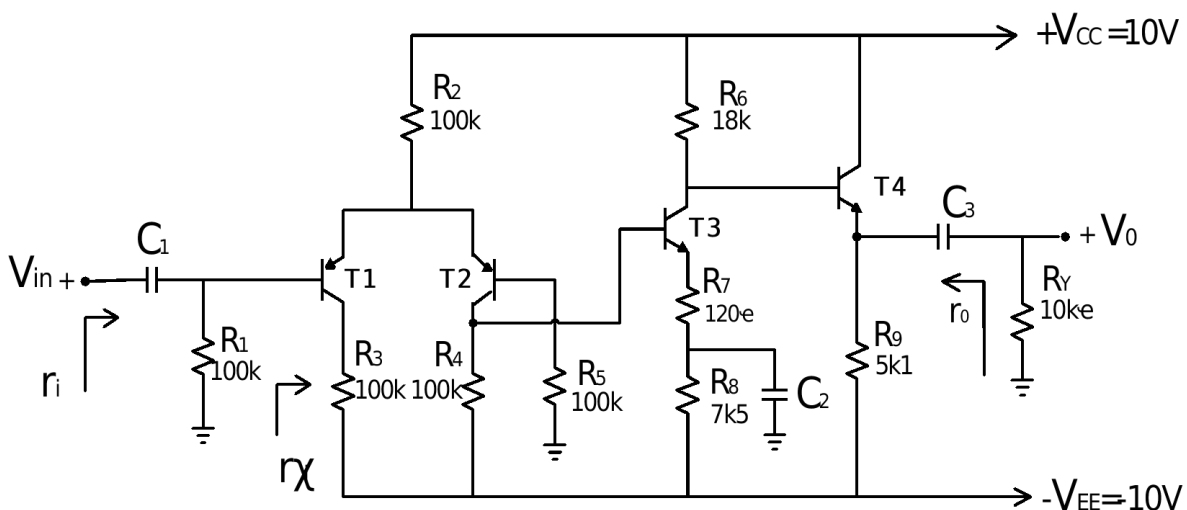


GOOD LUCK EVERYONE

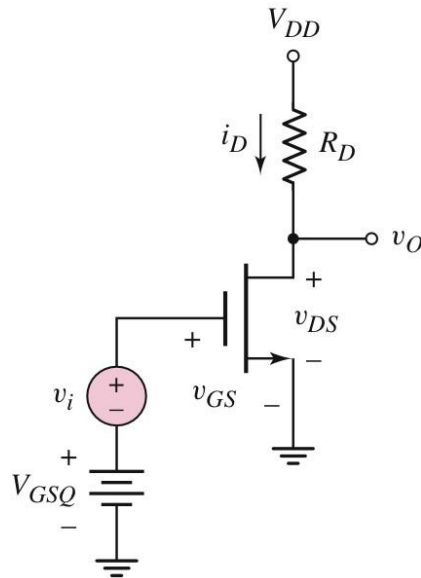
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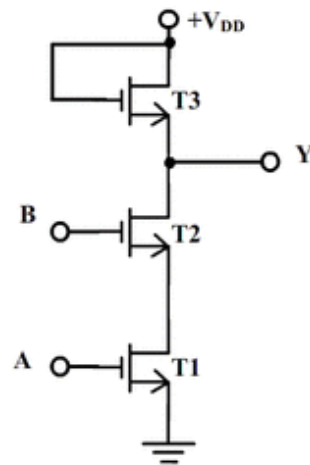
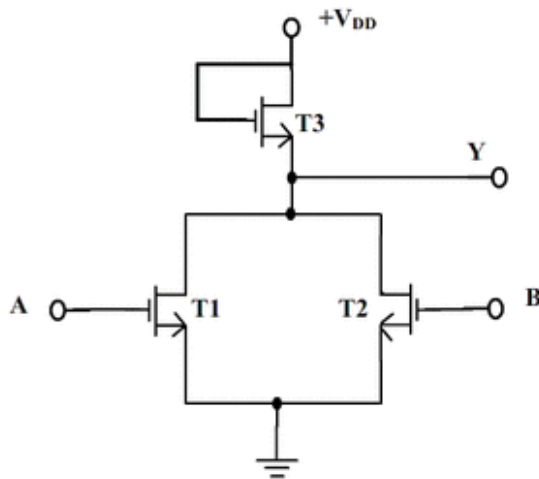
4. (35 points) Analyze the 3-stage amplifier circuit above. For all transistors $h_{FE}=h_{fe}=200$, $|V_{BE}| = 0,6V$, $h_{re} \cong 0$, $h_{oe} \cong 0$ and $V_T=25mV$.
- Find the collector currents of all 4 transistors.
 - Calculate the total voltage gain.
 - Calculate input resistance (r_i) and output resistance (r_o).
 - Calculate CMRR of the first stage.



5. Calculate the value of the R_D resistance so that the MOSFET transistor works in the saturation region. v_i is a small signal AC voltage source. $V_{DD}=10V$, $V_{GSQ}=4V$, $V_t=2V$, and $I_D=1mA$. (10 points)



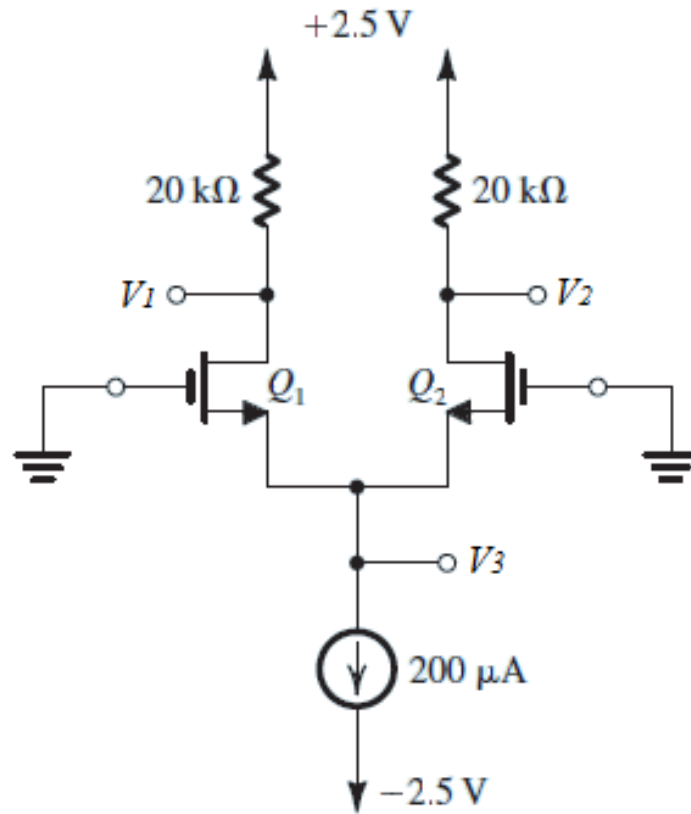
6. Consider the MOS digital gates shown below. Complete a truth table for each circuit and determine their function. (20 points)



7. (20 points) For the figure given below MOS parameters are

$V_{TH} = 0.7V$, $k_n' = \mu_n C_{ox} = 125 \left(\frac{\mu A}{V^2}\right)$. Find V_1 , V_2 and V_3 for (W/L) values given below.

- a. $(W/L)_1 = (W/L)_2 = 20$
 V_1 , V_2 ve V_3
 b. $(W/L)_1 = 1.5(W/L)_2 = 20$
 V_1 , V_2 ve V_3



Q1) +20V

Q2)

$$-30 + I_{B1} * R_{B1} + V_{BE1} = 0$$

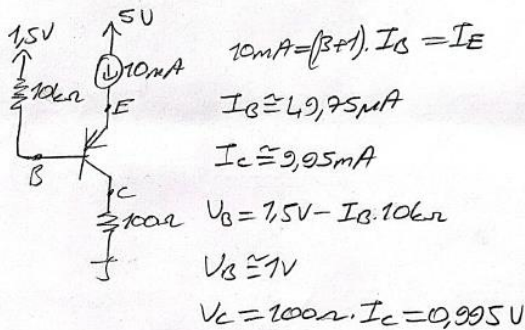
$$I_{B1} = \frac{30 - 0.7}{750 * 10^3} = 39.07 \mu A$$

$$I_{C1} = \beta * I_{B1} = 3.907 mA$$

$$R_i = r_{\pi} = \frac{V_t}{I_B} = 639.87 \Omega$$

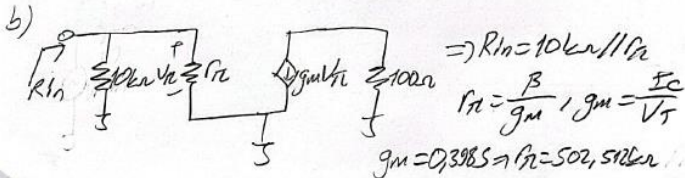
Q3:

a) DC analysis,



$$I_C = I_S \cdot \exp\left(\frac{V_{BE}}{V_T}\right) = 9.95 mA$$

$$V_E - V_B \approx 0.748V \Rightarrow V_E = 1.748V$$



$$R_{in} = 9.8046k\Omega$$

c)

$$V_{in} = V_{in} \cdot \frac{R_{in}}{R_{in} + 10k\Omega}, V_o = -g_m V_{in} (100\Omega)$$

$$\frac{V_o}{V_{in}} = -g_m \left(\frac{R_{in}}{R_{in} + 10k\Omega} \right) \cdot 100\Omega = -36.116 V/V$$

$$\pm 0.4V = V_o \Rightarrow V_{in} = \mp 11.075mV (V_{pp})$$

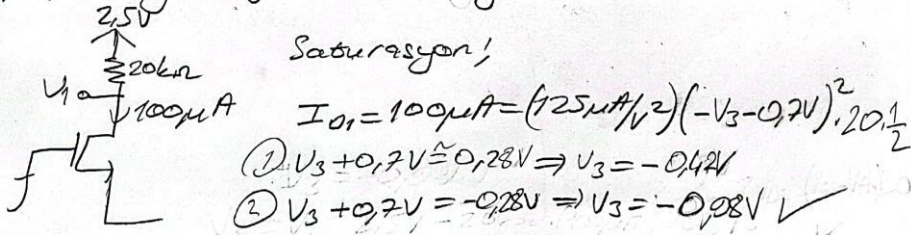
Q5) ANSWER: $R_D < (V_{DD} - (V_{GSQ} - V_T)) / I_D$

Q6) Answer the first is NOR the second NAND

Q7)

a) Mosfetlerin $\left(\frac{\mu}{L}\right)$ oranları, sarı terminallerindeki dirençler ve diğer terminallerindeki gerilimler eşit olduğuna göre, çalıştıkları bölge farketmemek için $200\mu A$ akımı eşit bölüşebileceklerdir.

Buna göre sadece bir mosfet üzerinden hesaplamalar yapıldı, hangi bölgede çalışıldığı bulunabilir.

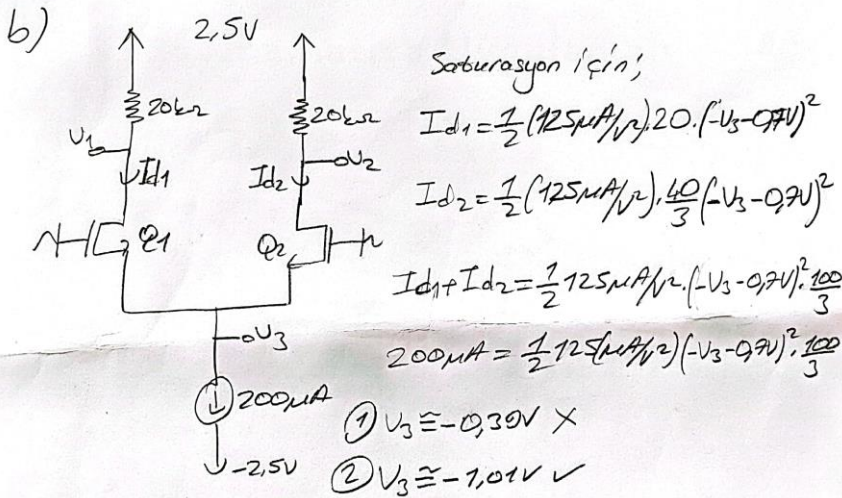


$$V_3 = -0.98V \text{ için } V_{GS} - V_{th} > 0V$$

$$V_1 = 2.5V - (20k\Omega) \cdot (100\mu A) = 0.5V$$

$V_{DS} (V_{GS} - V_{th}) > 0V \Rightarrow$ Mosfetlerin satürasyonda çalıştığı doğrulandı.

$$V_1 = V_2 = 0.5V, V_3 = -0.98V$$



$$V_3 = -1.01V \text{ için } V_{GS} - V_{th} > 0$$

$$V_1 = 2.5V - (20k\Omega) \cdot I_{D1} \Rightarrow I_{D1} = \frac{1}{2} (125\mu A/V^2) \cdot 20 \cdot (-1.01V - 0.7V)^2$$

$$I_{D1} = 120\mu A$$

$$V_1 = -0.1V \Rightarrow V_{DS1} = 0.1V - (-1.01V) = 1.11V > (1.01V - 0.7V)$$

Q1'in satürasyonda olduğu ispatlandı.

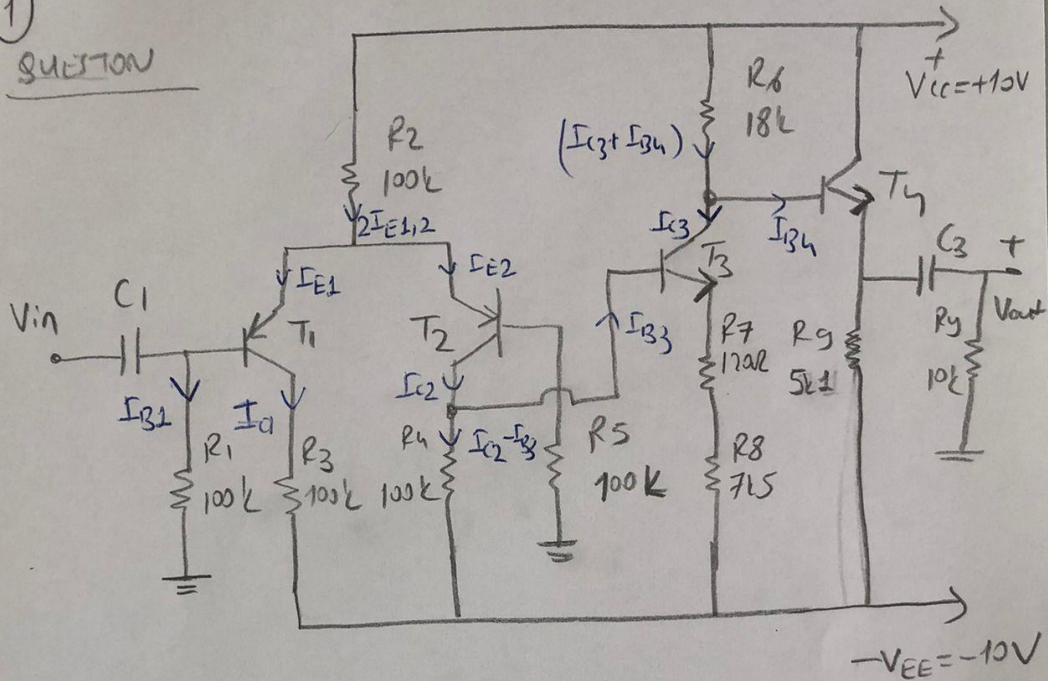
$$V_2 = 2.5V - (20k\Omega) \cdot (200\mu A - I_{D1}) = 0.9V \Rightarrow V_{DS2} = 0.9V - (-1.01V) = 1.91V$$

Q2'de satürasyondadır. $V_3 = -1.01V, V_1 = 0.1V, V_2 = 0.9V$

Q4)

①

QUESTION



$$h_{FE} = h_{FE} = 200, \quad |V_{BE}| = 0.6V, \quad V_T = 25mV$$

a) DC operation

$$\textcircled{1} \quad V_{CC} = 2I_{E1}R_2 + V_{EB1} + 100k \cdot I_{B1}$$

$$V_{CC} = 2(1+\beta)I_{B1} \cdot R_2 + V_{EB1} + 100k \cdot I_{B1}$$

$$I_{B1} = \frac{V_{CC} - V_{EB1}}{2(1+\beta)R_2 + 100k} = \frac{10V - 0.6V}{2 \cdot 201 \cdot 100k + 100k}$$

$$V_{EB1} = 0.6V$$

$$I_{C1} = h_{FE} \cdot I_{B1} = 0.047mA$$

$$I_{C1} = I_{C2} = 0.047mA$$

(2)

$$(2) \quad -100k \cdot (I_{C2} - I_{B3}) + V_{BE3} + (R_7 + R_8) \cdot I_{E3} = 0$$

$$-100k \cdot I_{C2} + 100k \cdot I_{B3} + V_{BE3} + (R_7 + R_8) (1 + \beta) I_{B3} = 0$$

$$I_{B3} = \frac{100k \cdot I_{C2} - V_{BE3}}{100k + (120\Omega + 7k5) \cdot 201} \Rightarrow I_{C3} = h_{FE} \cdot I_{B3}$$

$$I_{C3} = 0,5 \text{ mA}$$

$$(3) \quad 10V = 18k (I_{C3} + I_{B4}) + V_{BE4} + R_9 \cdot I_{E4}$$

$$10V = 18k \cdot I_{C3} + 18k \cdot I_{B4} + V_{BE4} + R_9 (1 + \beta) I_{B4}$$

$$I_{B4} = \frac{10V - V_{BE4} - 18k \cdot I_{C3}}{18k + (1 + \beta) \cdot R_9} \Rightarrow I_{C4} = h_{FE} \cdot I_{B4}$$

$$I_{C4} = 2 \text{ mA}$$

b) AC MODE

Kondansatörler ve bobinler kısa devre yapılır.

$$K_{v4} = \frac{R_{e4}}{r_{e4} + R_{e4}}$$

$$r_{i4} = h_{FE} (r_{e4} + R_{e4}) = 678k\Omega$$

$$R_{e4} = R_9 \parallel R_7 = 3,38k\Omega$$

$$r_{e1} = r_{e2} = 532\Omega$$

$$r_{e3} = 50\Omega$$

$$r_{e4} = 12,5\Omega$$

$$K_{v4} = \frac{3,38k\Omega}{12,5\Omega + 3,38k\Omega} = \underline{\underline{0,996}} = K_{v4}$$

T₃ için oluşan kuvvetlendirici için

$$K_{v3} = - \frac{R_6 // r_{i4}}{r_{e3} + R_7} = - \frac{18k // 678k\Omega}{50k + 120k} = \frac{17,5k\Omega}{170k}$$

(3)

$$K_{v3} = -103$$

$$r_{i3} = h_{fe3}(r_{e3} + R_{e3}) = 34k\Omega$$

Differential kat için $R_4 // r_{i3} = 25,4k\Omega$

$$K_{v2} = \frac{R_4 // r_{i3}}{2r_{e2} + \frac{R_5}{h_{fe2}}} = 16,2$$

$$K_{v2} = 16,2$$

$$K_v = K_{v2} \cdot K_{v3} \cdot K_{v1} = -1662$$

c) $r_i = R_2 // r_{i1} \Rightarrow r_{i1}' = 2h_{fe} r_{e1} + R_5 = 312,8k\Omega$

$$r_i = 100k // 312,8k\Omega = 75,8k\Omega$$

$$r_o = R_8 // \left(r_{e4} + \frac{R_6}{h_{fe}} \right) = 100,5k\Omega$$

d) $CMRR = 20 \log \left| \frac{2R_E + r_e}{r_e} \right| = 20 \log \left| \frac{2 \cdot 100k + 532\Omega}{532\Omega} \right|$

$$CMRR = 51,5 \text{ dB}$$